Preliminary

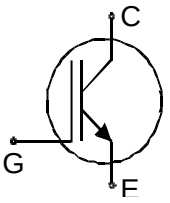
SIGC18T60SN

IGBT Chip in NPT-technology

FEATURES:
- 600V NPT technology
- 100µm chip
- short circuit prove
- positive temperature coefficient
- easy paralleling

This chip is used for:
- SGP20N60

Applications:
- drives



Chip Type	V_{CE}	I_{Cn}	Die Size	Package	Ordering Code
SIGC18T60SN	600V	20A	4.3 x 4.3 mm^2	sawn on foil	Q67041-S2856-A001

MECHANICAL PARAMETER:

Raster size	4.3 x 4.3	mm^2
Area total / active	18.49 / 14.3	
Emitter pad size	2.48 x 2.98	
Gate pad size	0.70 x 1.08	
Thickness	100	µm
Wafer size	125	mm
Flat position	270	deg
Max.possible chips per wafer	537	
Passivation frontside	Photoimide	
Emitter metalization	3200 nm Al Si 1%	
Collector metalization	1400 nm Ni Ag –system suitable for epoxy and soft solder die bonding	
Die bond	electrically conductive glue or solder	
Wire bond	Al, ≤500µm	
Reject Ink Dot Size	tbd	
Recommended Storage Environment	store in original container, in dry nitrogen, < 6 month	

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MAXIMUM RATINGS:

Parameter	Symbol	Value	Unit
Collector-emitter voltage	V_{CE}	600	V
DC collector current, limited by T_{jmax}	I_C	20	A
Pulsed collector current, t_p limited by T_{jmax}	I_{cpuls}	40	A
Gate emitter voltage	V_{GE}	±20	V
Operating junction and storage temperature	T_j, T_{stg}	-55 ... +150	°C

STATIC CHARACTERISTICS (tested on chip), T_j=25 °C, unless otherwise specified:

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
Collector-emitter breakdown voltage	$V_{(BR)CES}$	V_{GE}=0V , I_C=500µA	600			V
Collector-emitter saturation voltage	$V_{CE(sat)}$	V_{GE}=15V, I_C=20A	1.6	1.9	2.5	
Gate-emitter threshold voltage	$V_{GE(th)}$	I_C=500µA , V_{GE}=V_{CE}	3	4	5	
Zero gate voltage collector current	I_{CES}	V_{CE}=600V , V_{GE}=0V			70	µA
Gate-emitter leakage current	I_{GES}	V_{CE}=0V , V_{GE}=30V			120	nA

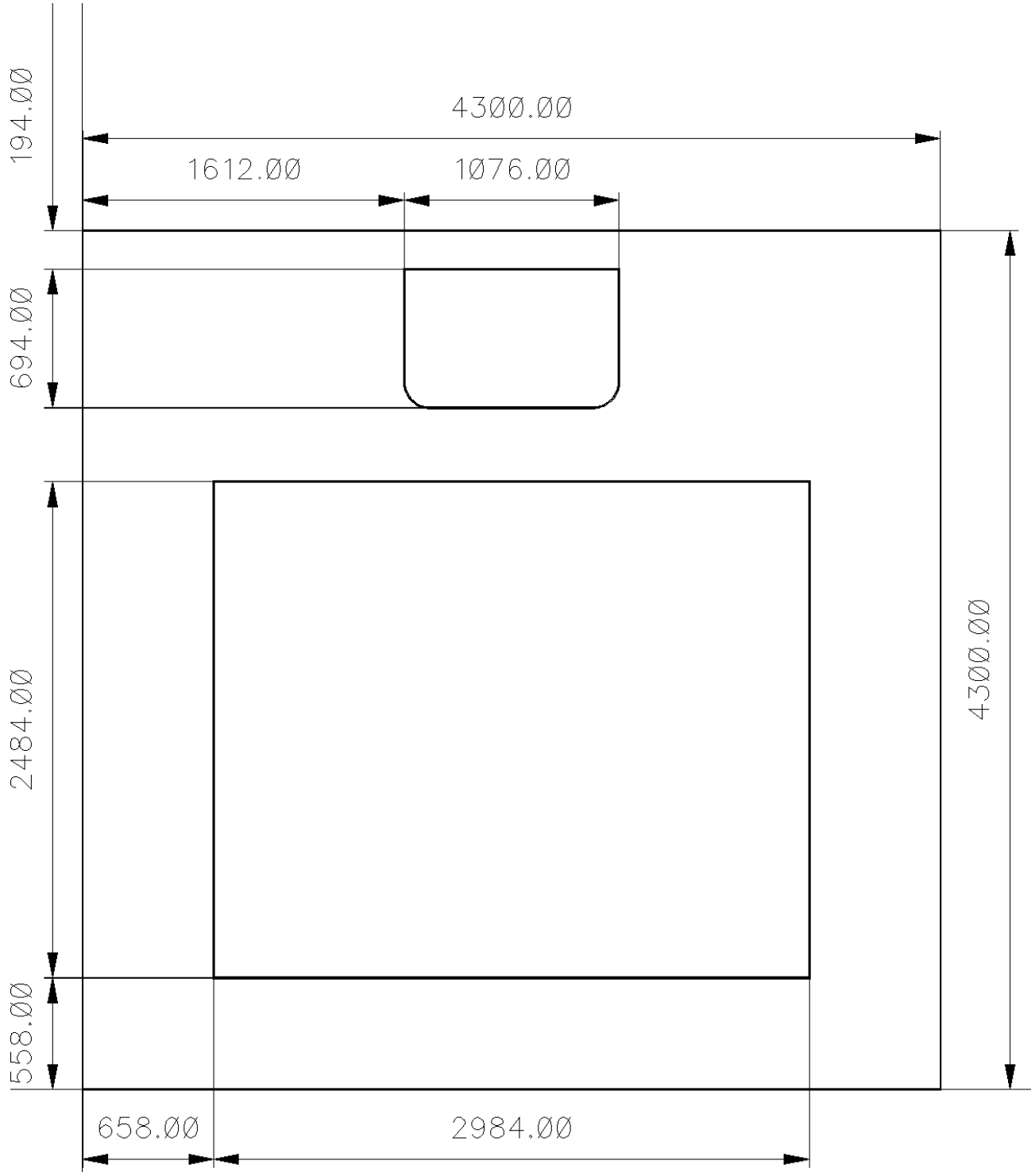
DYNAMIC CHARACTERISTICS (tested at component):

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
Input capacitance	C_{iss}	V_{CE}=25V,	-	1100	1320	pF
Output capacitance	C_{oss}	V_{GE}=0V,	-	107	128	
Reverse transfer capacitance	C_{rss}	f=1MHz	-	63	75	

SWITCHING CHARACTERISTICS (tested at component), Inductive Load:

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
Turn-on delay time	$t_{d(on)}$	T_j=25°C	-	24	29	ns
Rise time	t_r	V_{CC}=400V, I_C=20A	-	38	46	
Turn-off delay time	$t_{d(off)}$	V_{GE}=+15/0V,	-	225	270	
Fall time	t_f	R_G=16Ω	-	54	65	

CHIP DRAWING:



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FURTHER ELECTRICAL CHARACTERISTICS:

This chip data sheet refers to the device data sheet	SGP20N60	Package :TO220

Description:

AQL 0,65 for visual inspection according to failure catalog

Electrostatic Discharge Sensitive Device according to MIL-STD 883

Test-Normen Villach/Prüffeld

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